

SK280MB10



Half-Bridge (MOSFET module)

SK280MB10

Features*

- One screw mounting module
- Low inductive design
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- 100V Trench MOS technology
- UL recognized file no. E 63 532

Typical Applications

- Switched Mode Power Supplies

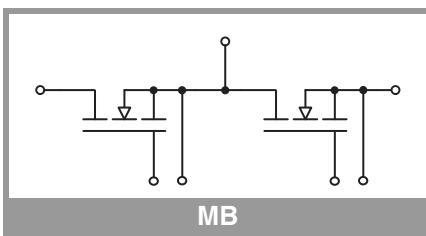
Remarks

Recommended driving for optimal switching performances: $V_{GS}=0/10V$

Absolute Maximum Ratings		Values	Unit
Symbol	Conditions		
MOSFET 1			
V_{DSS}		100	V
I_D	$T_j = 175^\circ\text{C}$	335	A
	$T_s = 25^\circ\text{C}$	280	A
I_{DM}		960	A
I_{DRM}		320	A
V_{GS}		-20 ... 20	V
T_j		-40 ... 175	$^\circ\text{C}$
Integrated body diode			
I_{FM}		960	A
I_{FRM}		320	A

Absolute Maximum Ratings		Values	Unit
Symbol	Conditions		
Module			
$I_{t(\text{RMS})}$	$\Delta T_{\text{terminal}}$ at PCB joint = 30 K, per pin	60	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC, sinusoidal, $t = 1$ min	2500	V

Characteristics		min.	typ.	max.	Unit
Symbol	Conditions				
MOSFET 1					
$V_{(\text{BR})DSS}$	$V_{GS} = 0$ V, $I_D = 1$ mA, $T_j = 25^\circ\text{C}$	100			V
$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 0.55$ mA, $T_j = 25^\circ\text{C}$	2	2.7	3.5	V
I_{DSS}	$V_{GS} = 0$ V, $V_{DS} = 100$ V, $T_j = 25^\circ\text{C}$		0.2		mA
I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = 20$ V, $T_j = 25^\circ\text{C}$		200		nA
$R_{DS(\text{on})}$	$V_{GS} = 10$ V	1.15	1.35		$\text{m}\Omega$
	$I_D = 200$ A		2.1		
	chiplevel				$\text{m}\Omega$
C_{iss}	$V_{GS} = 0$ V, $V_{DS} = 50$ V, $f = 1$ MHz	22200			pF
C_{oss}	$V_{GS} = 0$ V, $V_{DS} = 50$ V, $f = 1$ MHz	3880			pF
C_{rss}	$V_{GS} = 0$ V, $V_{DS} = 50$ V, $f = 1$ MHz	138			pF
R_{Gint}	$T_j = 25^\circ\text{C}$	4			Ω
Q_G	$V_{GS} = 0 \dots +15$ V, $V_{DD} = 50$ V, $I_D = 200$ A	530			nC
$t_{d(\text{on})}$	$V_{DD} = 50$ V	190			ns
$t_{d(\text{off})}$	$V_{GS} = 15/0$ V	1000			ns
t_r	$I_D = 200$ A	133			ns
t_f	R_G on/off = 15 Ω	97			ns
	di/dt _{off} = 1.6 kA/ μ s				
E_{on}	di/dt _{on} = 1.4 kA/ μ s	0.2			mJ
E_{off}	dv/dt = 637 kV/ μ s	2.1			mJ
$R_{th(j-s)}$	per MOSFET, $\lambda_{\text{paste}} = 0.8$ W/(mK)	0.47			K/W
Integrated body diode					
$V_F = V_{SD}$	$-I_D = 200$ A	0.88			V
	$V_{GS} = 0$ V	0.77			V
$V_{FO} = V_{SD0}$	chiplevel	0.71			V
		0.53			V
$r_F = r_{SD}$	chiplevel	0.85			$\text{m}\Omega$
		1.20			$\text{m}\Omega$
t_{rr}	$V_{DD} = 50$ V	90			ns
Q_{rr}	$-I_D = 200$ A	2.7			μC
I_{rr}	di/dt _{off} = 1.4 kA/ μ s	60			A
E_{rr}	$V_{GS} = 0$ V	0.1			mJ





Characteristics		Symbol	Conditions	min.	typ.	max.	Unit
Module							
L_{CE}					5		nH
M_s	to heatsink			2.25		2.5	Nm
w	weight				29		g

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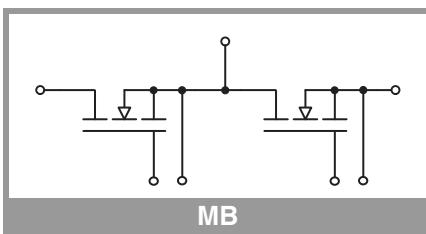
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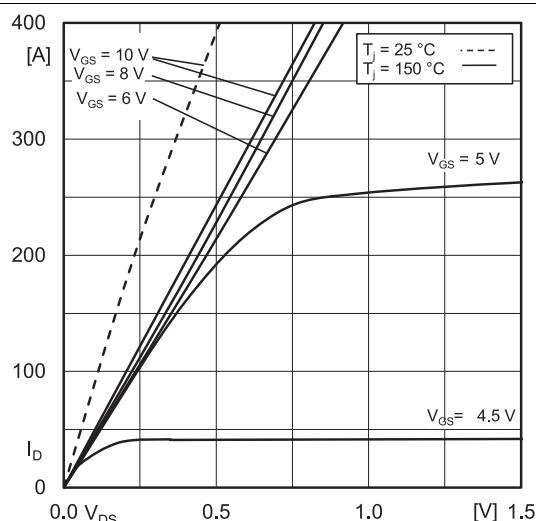


Fig.1: Typ. MOSFET forward output characteristic, incl.
 $R_{DD'} + SS'$

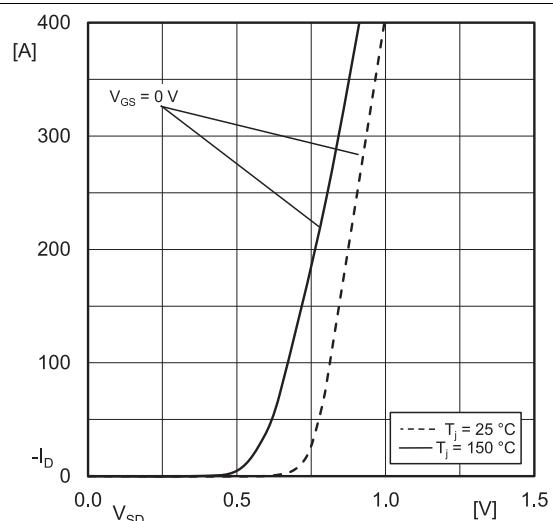


Fig. 2: Typ. reverse output characteristic, incl. $R_{DD'} + SS'$

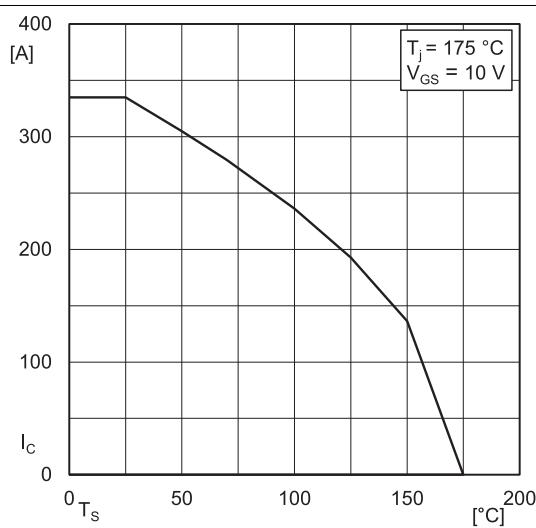


Fig. 3: Rated current vs. temperature $I_D = f (T_S)$

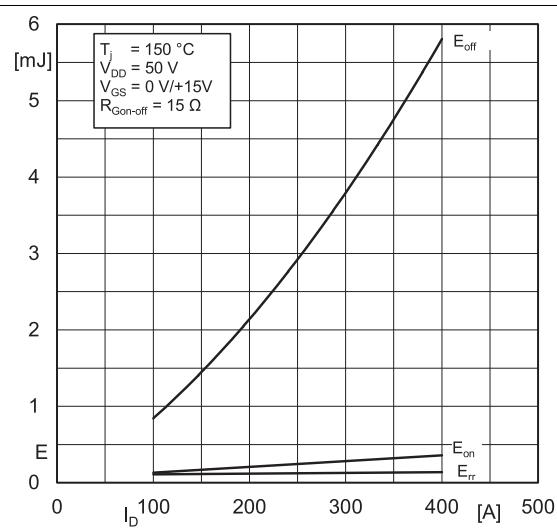


Fig. 4: Typ. turn-on/-off energy $E = f(I_D)$

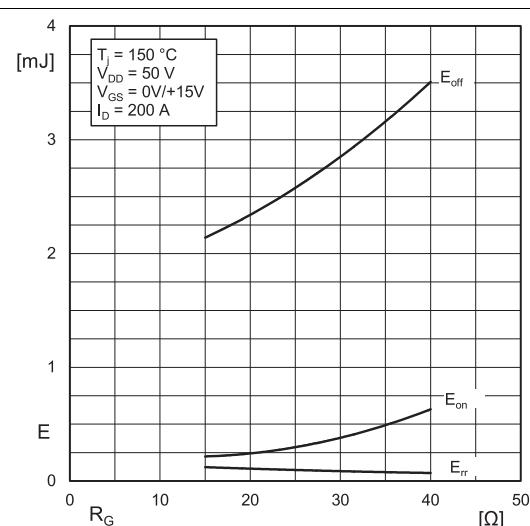


Fig. 5: Typ. turn-on /-off energy $E= f (R_G)$

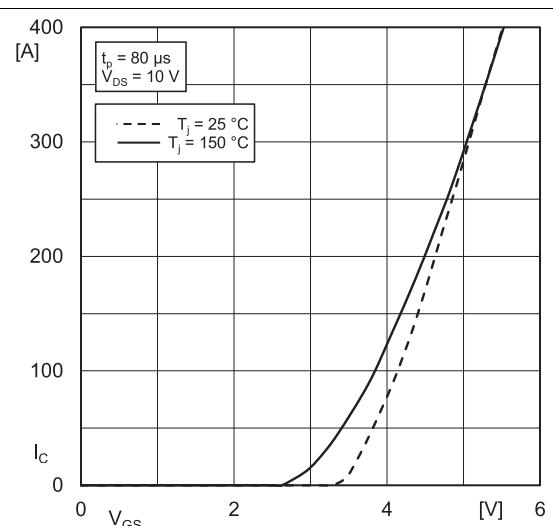


Fig. 6: Typ. MOSFET transfer characteristic

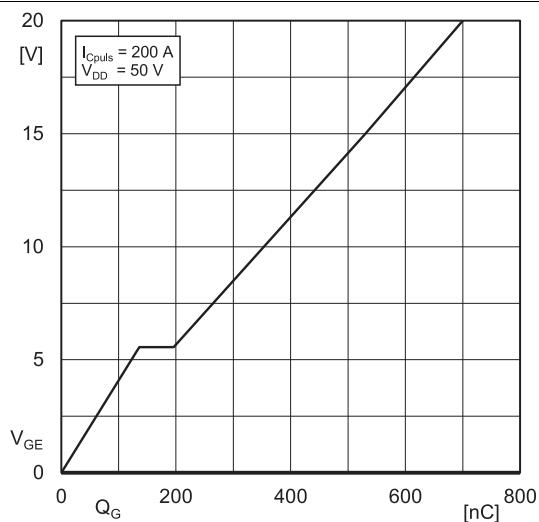


Fig. 7: Typ. MOSFET gate charge characteristic

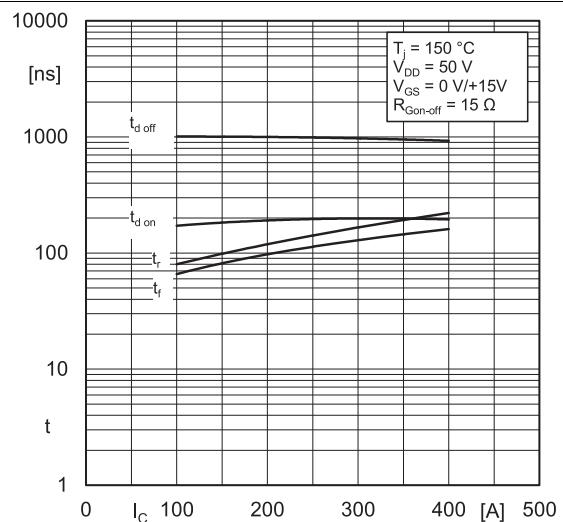


Fig. 8: Typ. switching times vs. I_D

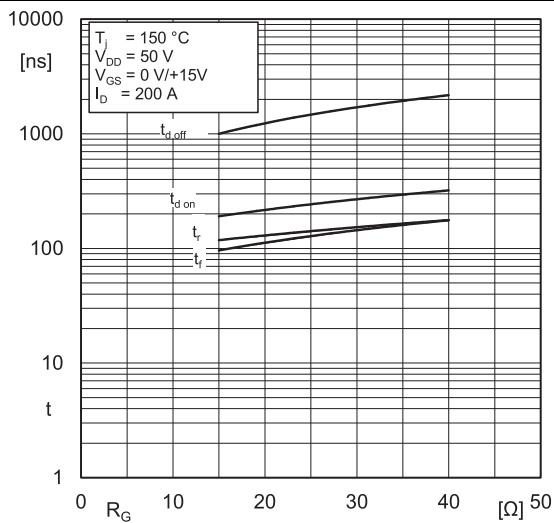


Fig. 9: Typ. switching times vs. gate resistor R_G

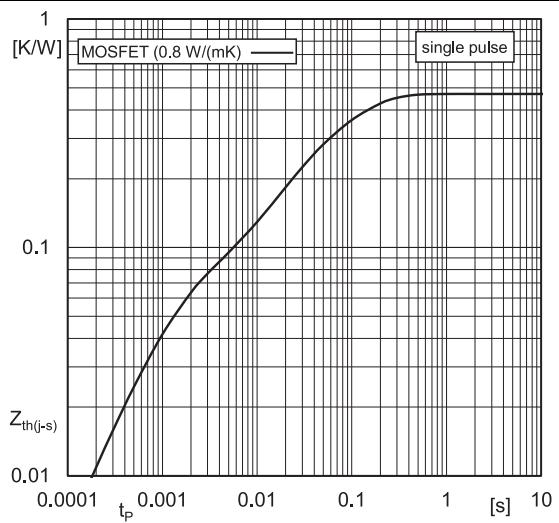
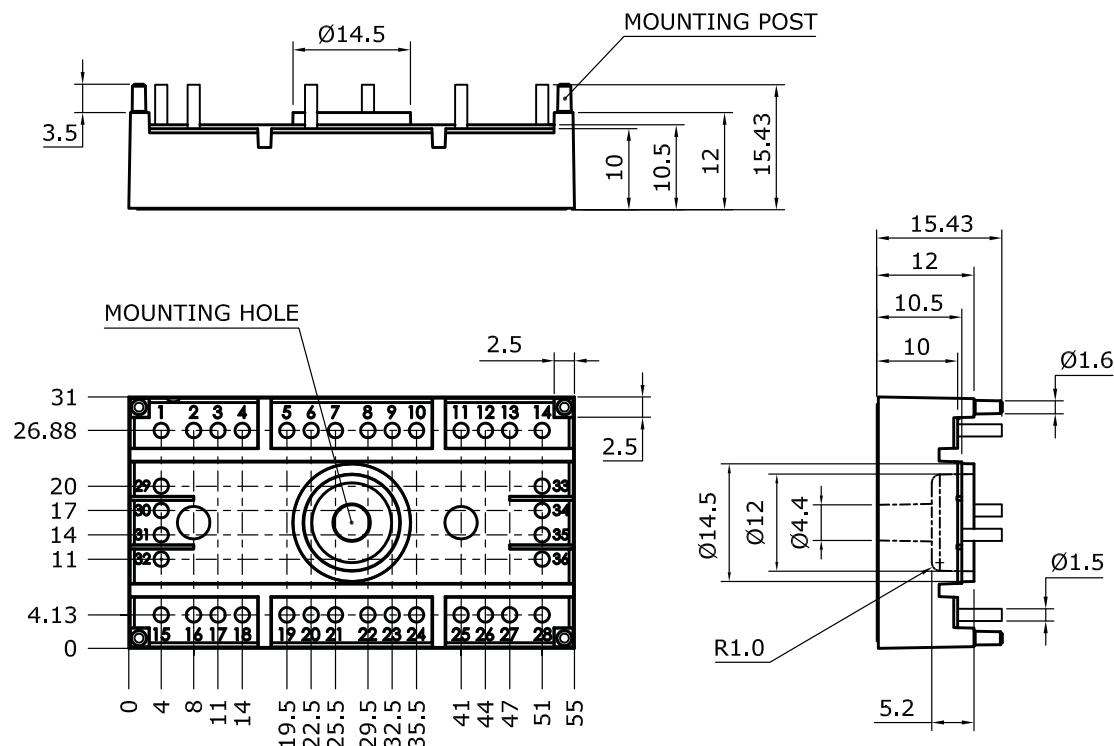


Fig. 10: Typ. transient thermal impedance

Dimensions: mm
Tolerance system: ISO 2768-m



Suggested hole diameter for solder pins in the circuit board:

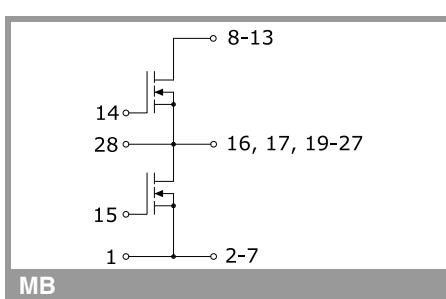
- 2.0 mm

Suggested hole diameter for the mounting post in the circuit board:

- 2.0 mm

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SEMITOP®3



This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

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